SCT2080KE

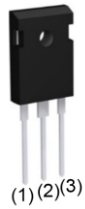
N-channel SiC power MOSFET

Datasheet

V_{DSS}	1200V
$R_{DS(on)}$ (Typ.)	80mΩ
I_D	40A

●Outline

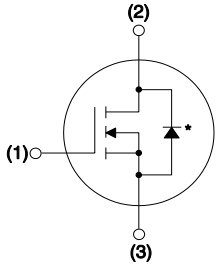
TO-247N



●Features

1) Low on-resistance
2) Fast switching speed
3) Fast reverse recovery
4) Easy to parallel
5) Simple to drive
6) Pb-free lead plating ; RoHS compliant

●Inner circuit



(1) Gate
(2) Drain
(3) Source

* Body Diode

●Application

・Solar inverters
・DC/DC converters
・Induction heating
・Motor drives

●Packaging specifications

Package		TO-247N
Type	Packing	Tube
	Reel size (mm)	-
	Tape width (mm)	-
	Basic ordering unit (pcs)	30
	Packing code	C11
	Marking	SCT2080KE

●Absolute maximum ratings (T_a = 25°C)

Parameter		Symbol	Value	Unit
Drain - Source voltage		V_{DSS}	1200	V
Continuous drain current	T_c = 25°C	I_D *1	40	A
	T_c = 100°C	I_D *1	28	A
Pulsed drain current		$I_{D,pulse}$ *2	80	A
Gate - Source voltage (DC)		V_{GSS}	−6 to +22	V
Gate - Source surge voltage (t_{surge} < 300nsec)		V_{GSS_surge} *3	−10 to +26	V
Total power dissipation	T_C=25°C, See Fig.1	P_D	262	W
	T_C=100°C, See Fig.1		130	W
Junction temperature		T_j	175	°C
Range of storage temperature		T_{stg}	−55 to +175	°C

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●Electrical characteristics (T_a = 25°C)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Drain - Source breakdown voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 1mA	1200	-	-	V
Zero gate voltage drain current	I_{DSS}	V_{DS} = 1200V, V_{GS} = 0V				μA
		T_j = 25°C	-	1	10	
		T_j = 150°C	-	2	-	
Gate - Source leakage current	I_{GSS+}	V_{GS} = +22V, V_{DS} = 0V	-	-	100	nA
Gate - Source leakage current	I_{GSS-}	V_{GS} = -6V, V_{DS} = 0V	-	-	-100	nA
Gate threshold voltage	$V_{GS\ (th)}$	V_{DS} = V_{GS}, I_D = 4.4mA	1.6	2.8	4.0	V

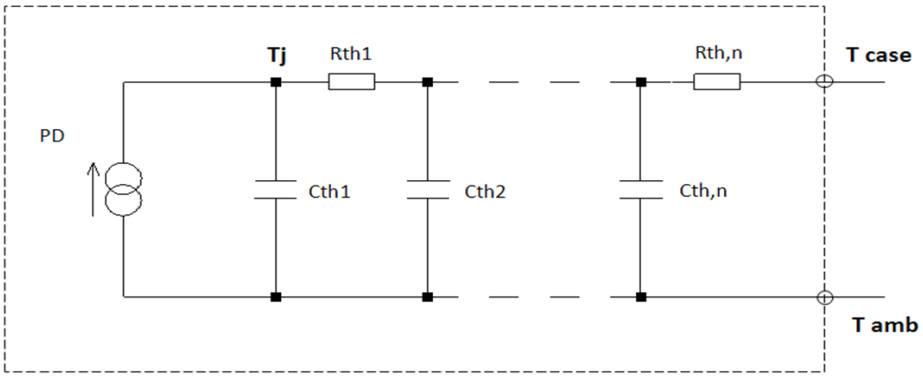
●Thermal resistance

Parameter	Symbol	Values			Unit
		Min.	Typ.	Max.	
Thermal resistance, junction - case	R_{thJC}	-	0.44	0.57	°C/W

●Typical Transient Thermal Characteristics

Symbol	Value	Unit
R_{th1}	7.80E-02	K/W
R_{th2}	1.97E-01	
R_{th3}	1.62E-01	

Symbol	Value	Unit
C_{th1}	5.00E-03	Ws/K
C_{th2}	1.80E-02	
C_{th3}	2.49E-01	



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●Electrical characteristics (T_a = 25°C)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Static drain - source on - state resistance	$R_{DS(on)}$ *4	V_{GS} = 18V, I_D = 10A T_j = 25°C	-	80	117	mΩ
		T_j = 125°C	-	125	-	
Gate input resistance	R_G	f = 1MHz, open drain	-	6.3	-	Ω
Transconductance	g_{fs} *4	V_{DS} = 10V, I_D = 10A	-	3.7	-	S
Input capacitance	C_{iss}	V_{GS} = 0V	-	2080	-	pF
Output capacitance	C_{oss}	V_{DS} = 800V	-	77	-	
Reverse transfer capacitance	C_{rss}	f = 1MHz	-	16	-	
Effective output capacitance, energy related	$C_{o(er)}$	V_{GS} = 0V V_{DS} = 0V to 500V	-	116	-	pF
Turn - on delay time	$t_{d(on)}$ *4	V_{DD} = 400V, V_{GS} = 18V	-	35	-	ns
Rise time	t_r *4	I_D = 10A	-	36	-	
Turn - off delay time	$t_{d(off)}$ *4	R_L = 40Ω	-	76	-	
Fall time	t_f *4	R_G = 0Ω	-	22	-	
Turn - on switching loss	E_{on} *4	V_{DD} = 600V, I_D=10A V_{GS} = 18V/0V R_G = 0Ω, L=500μH *E_{on} includes diode reverse recovery	-	174	-	μJ
Turn - off switching loss	E_{off} *4		-	51	-	

●Gate Charge characteristics (T_a = 25°C)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Total gate charge	Q_g *4	V_{DD} = 400V	-	106	-	nC
Gate - Source charge	Q_{gs} *4	I_D = 10A	-	27	-	
Gate - Drain charge	Q_{gd} *4	V_{GS} = 18V	-	31	-	
Gate plateau voltage	$V_{(plateau)}$	V_{DD} = 400V, I_D = 10A	-	9.7	-	V

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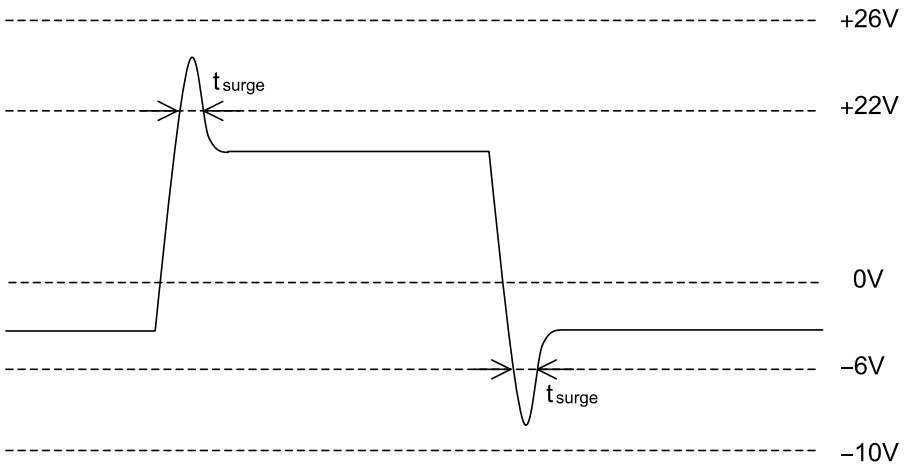
●**Body diode electrical characteristics** (Source-Drain) (T_a = 25°C)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Body diode continuous, forward current	I_S *1	T_c = 25°C	-	-	40	A
Body diode direct current, pulsed	I_{SM} *2		-	-	80	A
Forward voltage	V_{SD} *4	V_{GS} = 0V, I_S = 10A	-	4.6	-	V
Reverse recovery time	t_{rr} *4	I_F = 10A, V_R = 400V di/dt = 150A/μs	-	31	-	ns
Reverse recovery charge	Q_{rr} *4		-	44	-	nC
Peak reverse recovery current	I_{rrm} *4		-	2.3	-	A

*1 Limited only by maximum temperature allowed.

*2 PW ≤ 10μs, Duty cycle ≤ 1%

*3 Example of acceptable V_{GS} waveform



*4 Pulsed

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●Electrical characteristic curves

Fig.1 Power Dissipation Derating Curve

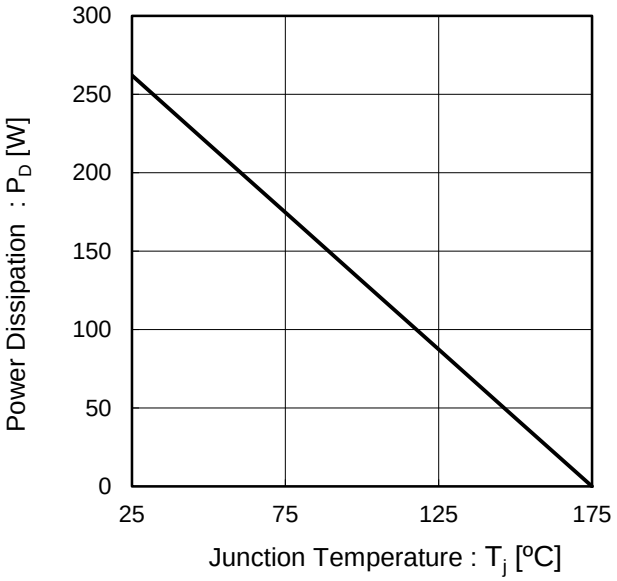


Fig.2 Maximum Safe Operating Area

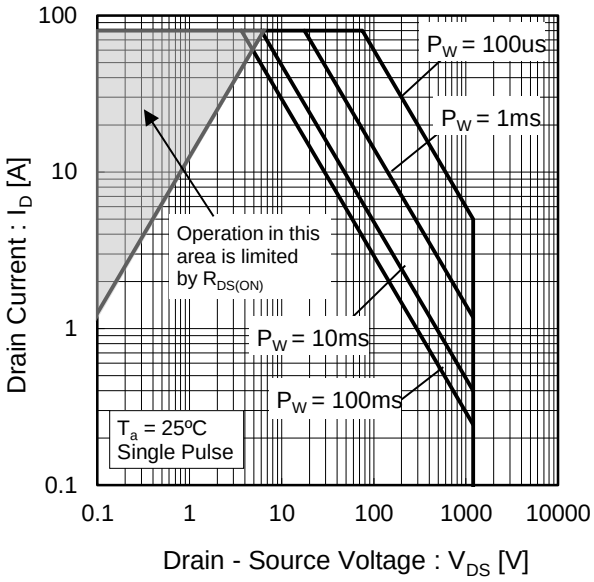
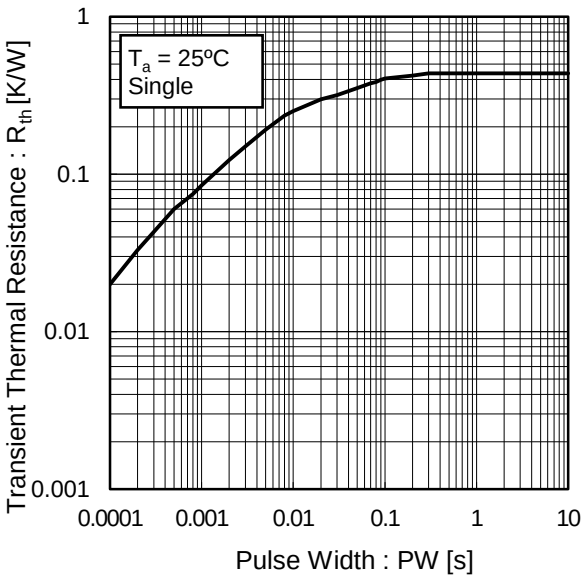


Fig.3 Typical Transient Thermal Resistance vs. Pulse Width



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●Electrical characteristic curves

Fig.4 Typical Output Characteristics(I)

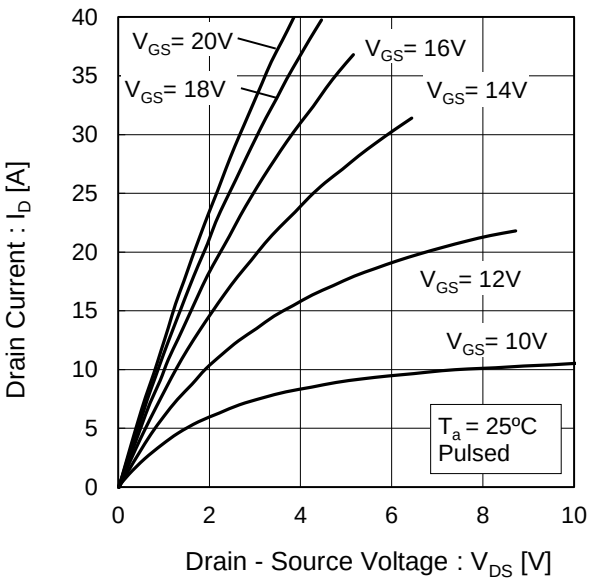


Fig.5 Typical Output Characteristics(II)

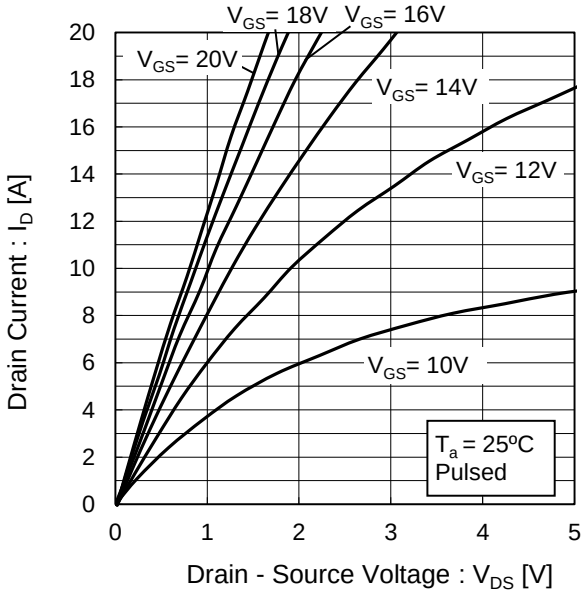


Fig.6 Typical Output Characteristics(I)

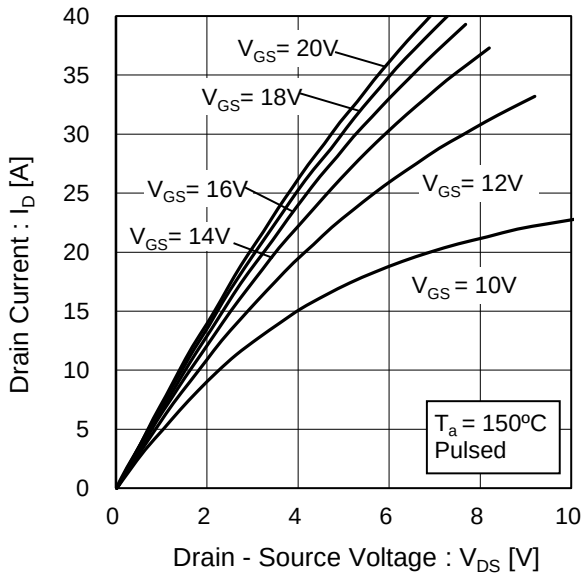
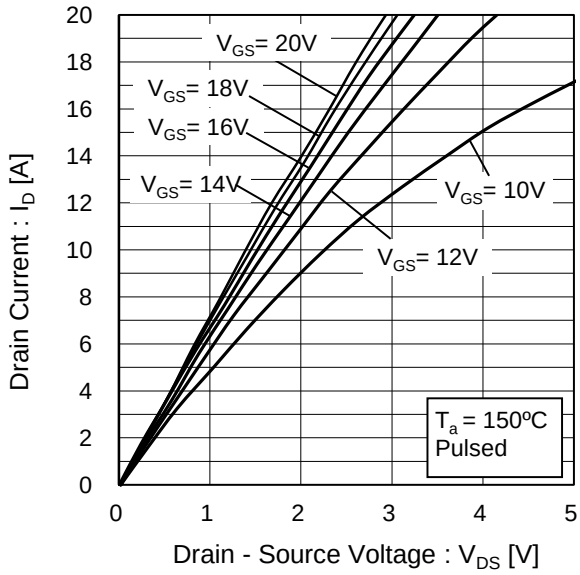


Fig.7 Typical Output Characteristics(II)



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●Electrical characteristic curves

Fig.8 Typical Transfer Characteristics

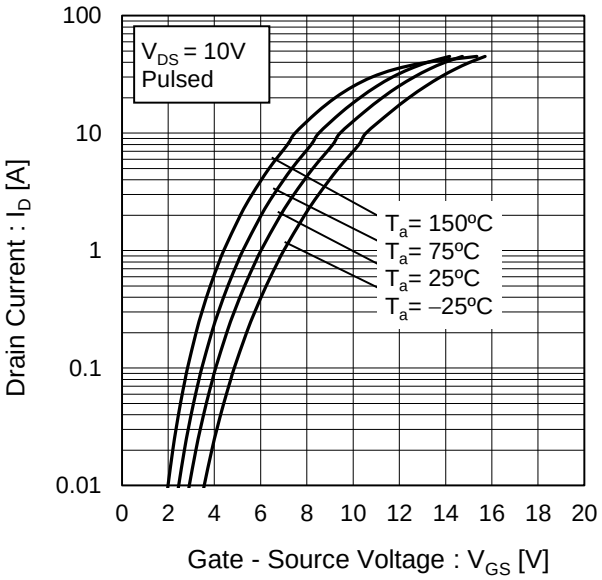


Fig.9 Typical Transfer Characteristics (II)

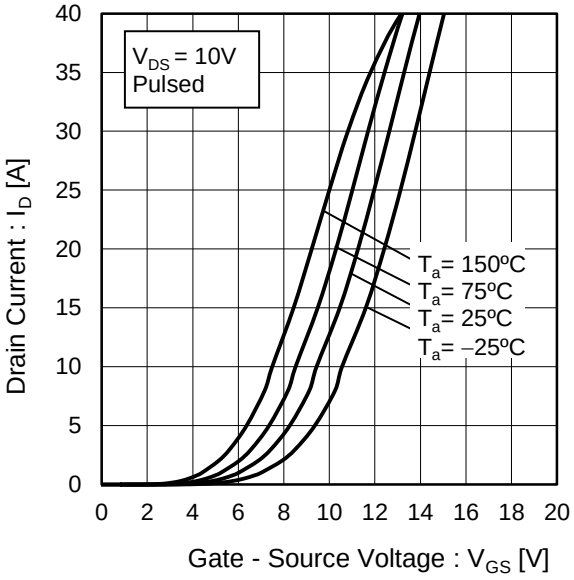


Fig.10 Gate Threshold Voltage vs. Junction Temperature

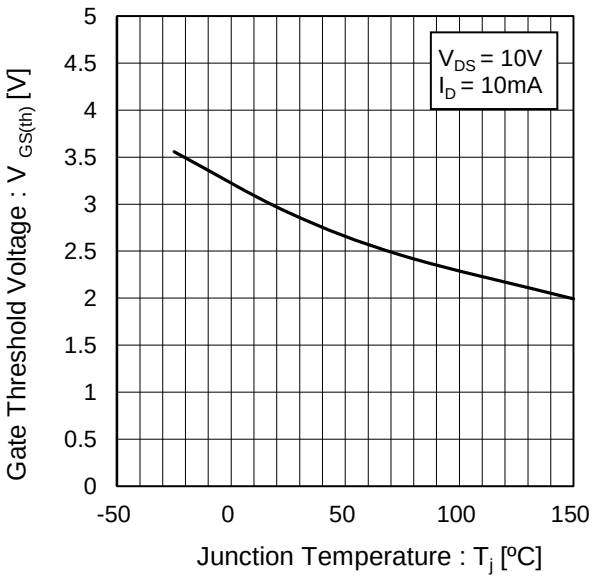
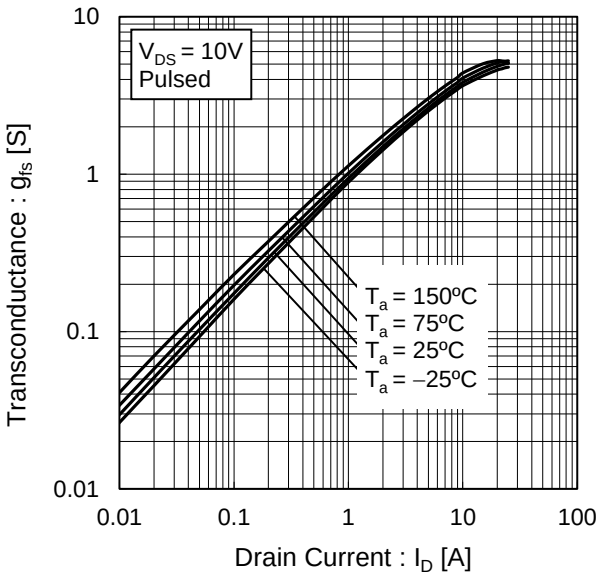


Fig.11 Transconductance vs. Drain Current



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●Electrical characteristic curves

Fig.12 Static Drain - Source On - State Resistance vs. Gate - Source Voltage

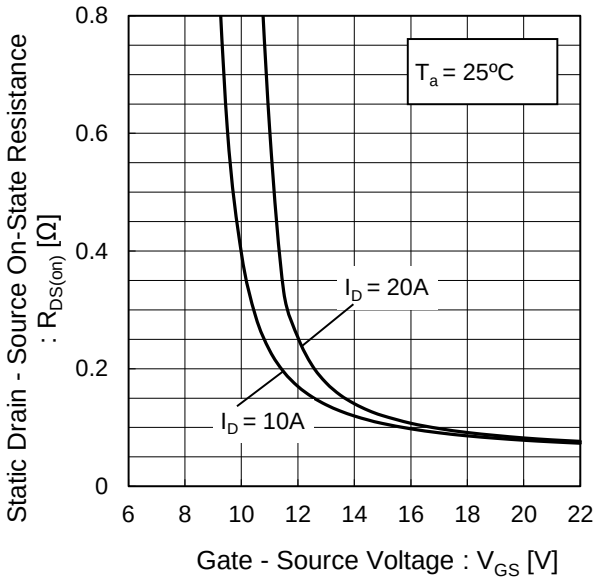


Fig.13 Static Drain - Source On - State Resistance vs. Junction Temperature

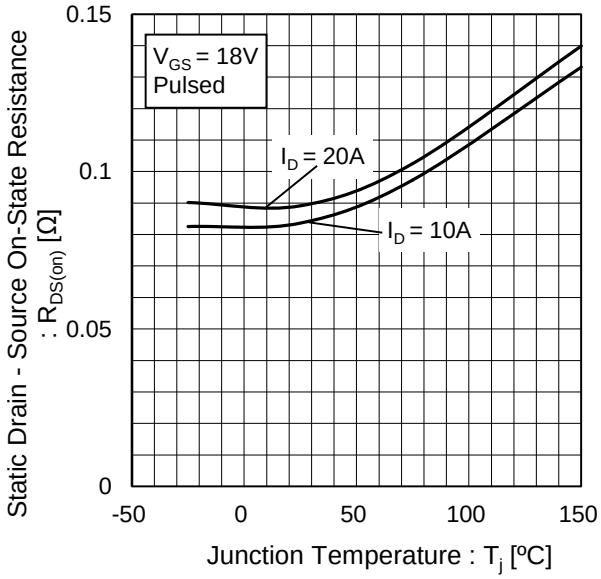
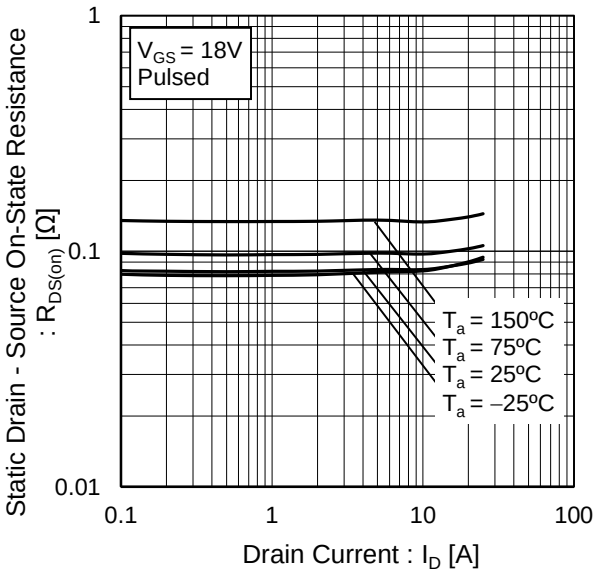


Fig.14 Static Drain - Source On - State Resistance vs. Drain Current



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●Electrical characteristic curves

Fig.15 Typical Capacitance vs. Drain - Source Voltage

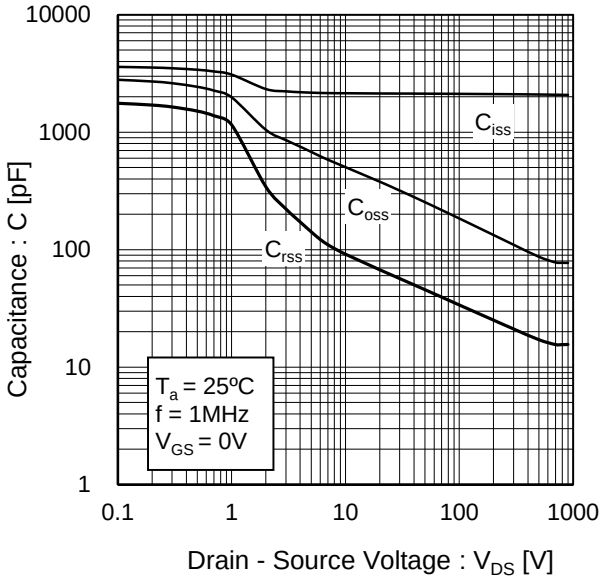


Fig.16 C_{oss} Stored Energy

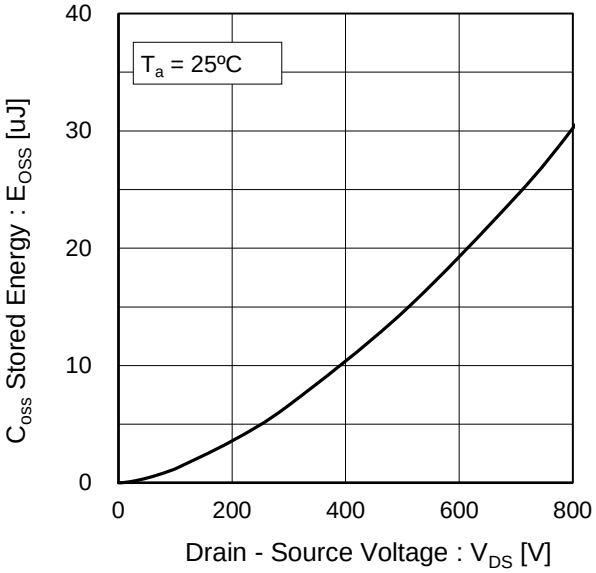


Fig.17 Switching Characteristics

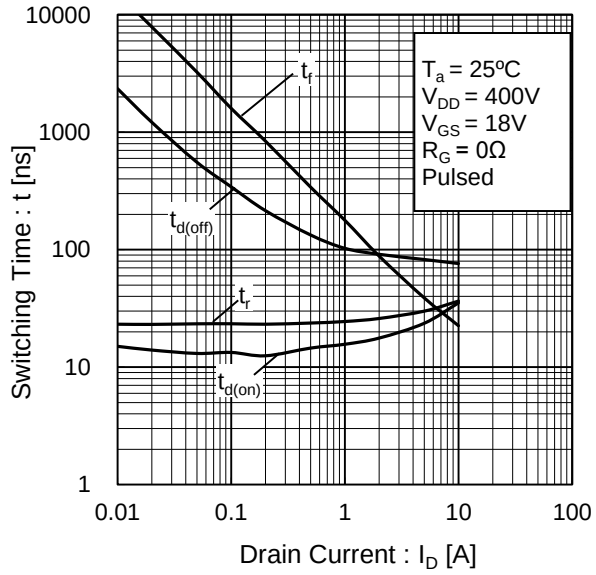
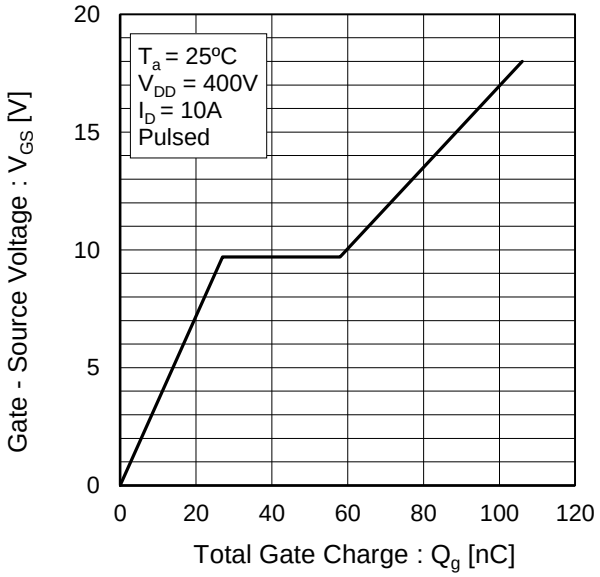


Fig.18 Dynamic Input Characteristics



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●Electrical characteristic curves

Fig.19 Typical Switching Loss vs. Drain - Source Voltage

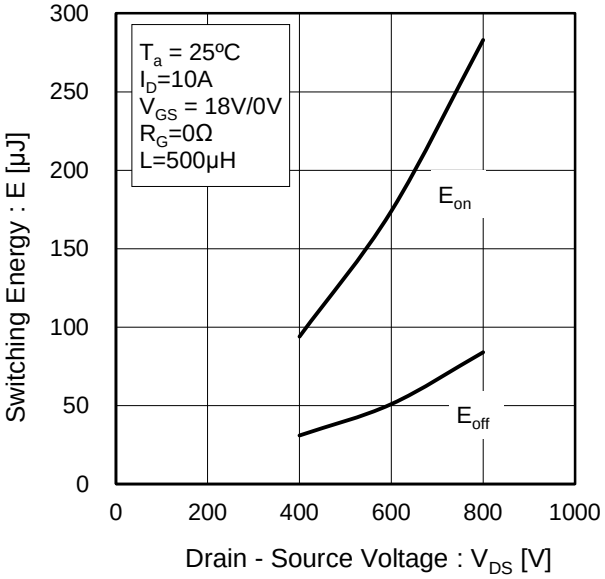


Fig.20 Typical Switching Loss vs. Drain Current

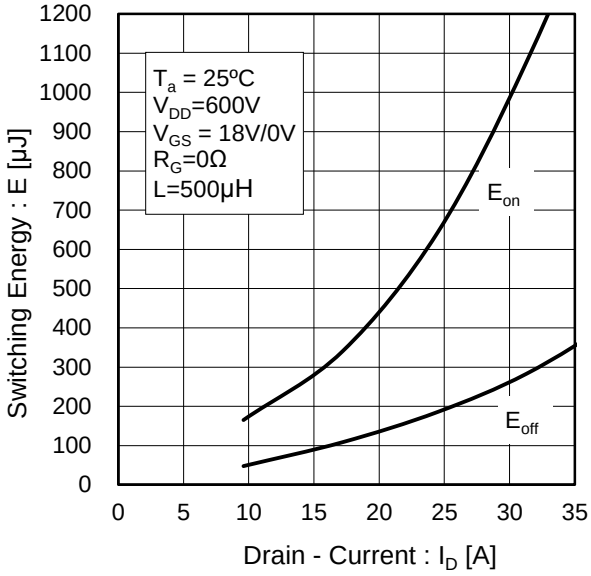
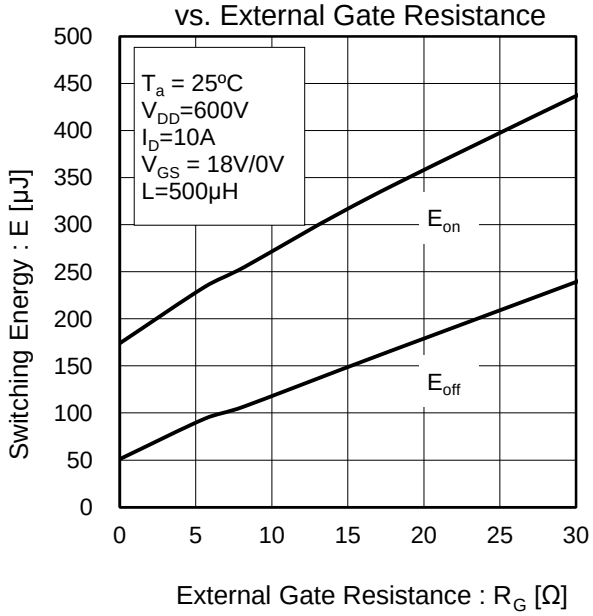


Fig.21 Typical Switching Loss vs. External Gate Resistance



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●Electrical characteristic curves

Fig.22 Body Diode Forward Current vs. Source - Drain Voltage

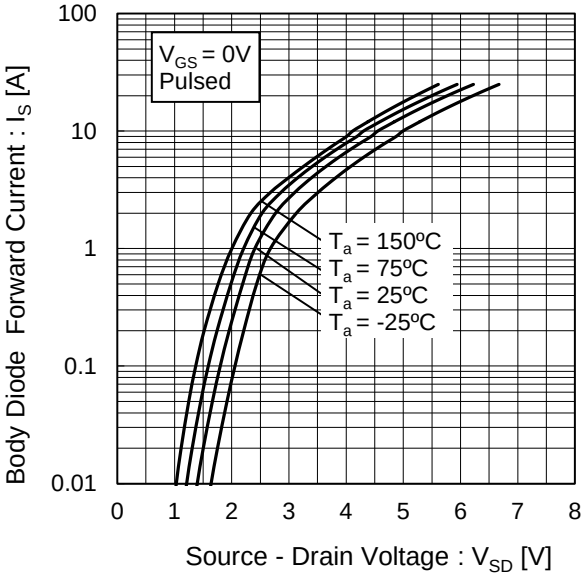
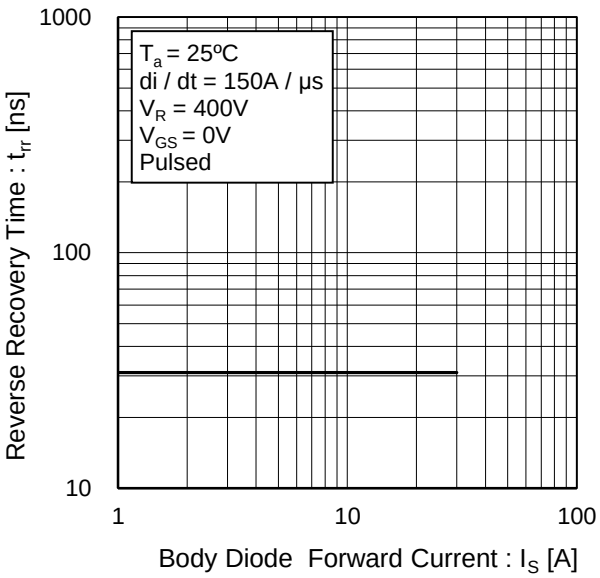


Fig.23 Reverse Recovery Time vs.Body Diode Forward Current



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●Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

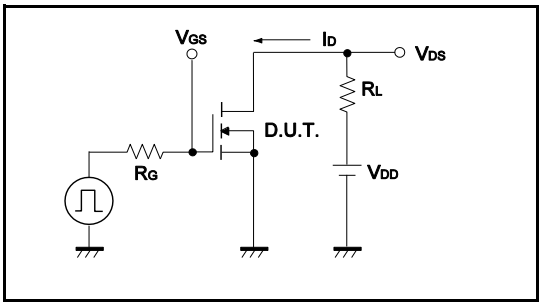


Fig.1-2 Switching Waveforms

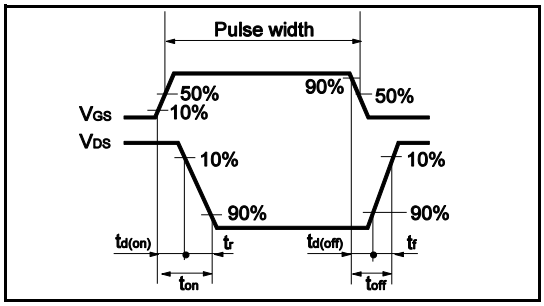


Fig.2-1 Gate Charge Measurement Circuit

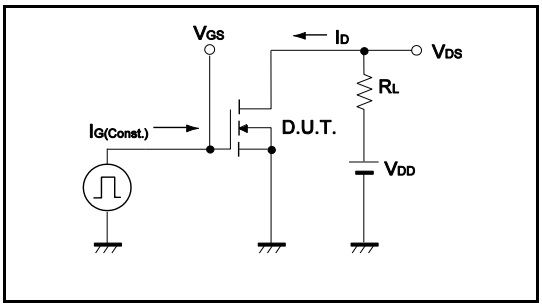


Fig.2-2 Gate Charge Waveform

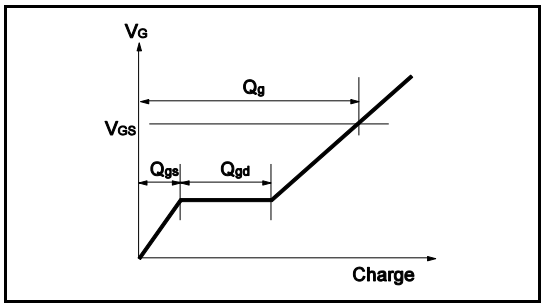


Fig.3-1 Switching Energy Measurement Circuit

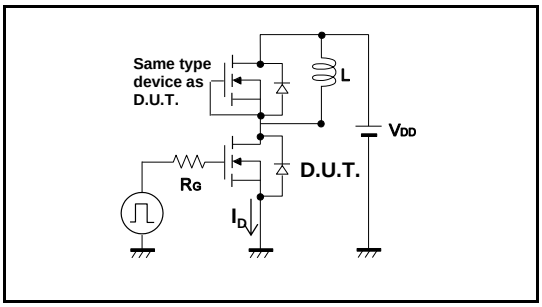


Fig.3-2 Switching Waveforms

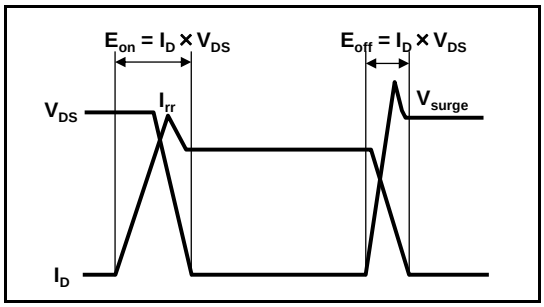


Fig.4-1 Reverse Recovery Time Measurement Circuit

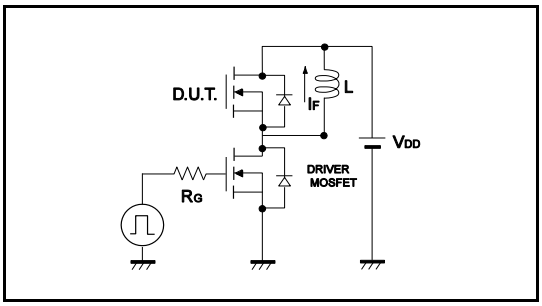
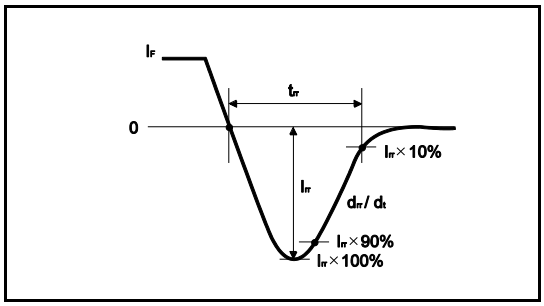


Fig.4-2 Reverse Recovery Waveform



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Entegreci, Eskişehir merkezli, Türkiye geneline satış yapan bir elektronik komponent mağazasıdır. Entegreler (IC), mikrodenetleyiciler, transistörler, diyotlar, pasif elemanlar, konnektörler, modüller ve geliştirme kartları tek adetten seri üretim adetlerine kadar satılır. Ürün sayfalarında güncel stok durumunu, fiyatı ve datasheet bağlantısını bulabilirsiniz.

Parça koduyla arama

Üretici parça numarasını yazın; stok ve fiyatı hemen görün.

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Ürün kategorileri

Entegreden kapasitöre tüm elektronik komponent kategorileri.

Kategorilere göz atın

Üreticiler

Aradığınız üreticinin ürünlerini tek sayfada inceleyin.

Üreticileri görün

Toplu alım ve teklif

Listede olmayan ya da yüksek adetli parçalar için teklif isteyin.

Teklif isteyin

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Entegreci is an online electronic components store based in Türkiye. Search by manufacturer part number to see stock, prices and datasheets for integrated circuits, microcontrollers, transistors, passive components and connectors, or request a quote for parts that are not listed.

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